

Won Jong Yoo

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167
papers

7,078
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41
h-index

81
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183
ext. papers

8,269
ext. citations

7.2
avg, IF

5.82
L-index

#	Paper	IF	Citations
167	Flexible and transparent MoS ₂ field-effect transistors on hexagonal boron nitride-graphene heterostructures. <i>ACS Nano</i> , 2013 , 7, 7931-6	16.7	800
166	High-performance perovskite-graphene hybrid photodetector. <i>Advanced Materials</i> , 2015 , 27, 41-6	24	651
165	Controlled charge trapping by molybdenum disulphide and graphene in ultrathin heterostructured memory devices. <i>Nature Communications</i> , 2013 , 4, 1624	17.4	504
164	Lateral MoS ₂ p-n junction formed by chemical doping for use in high-performance optoelectronics. <i>ACS Nano</i> , 2014 , 8, 9332-40	16.7	419
163	Highly stretchable piezoelectric-pyroelectric hybrid nanogenerator. <i>Advanced Materials</i> , 2014 , 26, 765-9	24	382
162	Fermi Level Pinning at Electrical Metal Contacts of Monolayer Molybdenum Dichalcogenides. <i>ACS Nano</i> , 2017 , 11, 1588-1596	16.7	379
161	Ultimate thin vertical p-n junction composed of two-dimensional layered molybdenum disulfide. <i>Nature Communications</i> , 2015 , 6, 6564	17.4	231
160	P-Type Polar Transition of Chemically Doped Multilayer MoS ₂ Transistor. <i>Advanced Materials</i> , 2016 , 28, 2345-51	24	141
159	Modulation of Quantum Tunneling via a Vertical Two-Dimensional Black Phosphorus and Molybdenum Disulfide p-n Junction. <i>ACS Nano</i> , 2017 , 11, 9143-9150	16.7	113
158	Carrier-Type Modulation and Mobility Improvement of Thin MoTe. <i>Advanced Materials</i> , 2017 , 29, 16064334	24	111
157	Colossal grain growth yields single-crystal metal foils by contact-free annealing. <i>Science</i> , 2018 , 362, 1021-1025	339	107
156	Highly Oriented Monolayer Graphene Grown on a Cu/Ni(111) Alloy Foil. <i>ACS Nano</i> , 2018 , 12, 6117-6127	16.7	100
155	Transferred via contacts as a platform for ideal two-dimensional transistors. <i>Nature Electronics</i> , 2019 , 2, 187-194	28.4	90
154	Nonvolatile flash memory device using Ge nanocrystals embedded in HfAlO high- κ /tunneling and control oxides: Device fabrication and electrical performance. <i>IEEE Transactions on Electron Devices</i> , 2004 , 51, 1840-1848	2.9	90
153	Metal-semiconductor barrier modulation for high photoresponse in transition metal dichalcogenide field effect transistors. <i>Scientific Reports</i> , 2014 , 4, 4041	4.9	85
152	Schottky-barrier S/D MOSFETs with high-k gate dielectrics and metal-gate electrode. <i>IEEE Electron Device Letters</i> , 2004 , 25, 268-270	4.4	83
151	Crystalline zirconia oxide on silicon as alternative gate dielectrics. <i>Applied Physics Letters</i> , 2001 , 78, 1604-1606	3.1	82

150	Si-compatible cleaning process for graphene using low-density inductively coupled plasma. <i>ACS Nano</i> , 2012 , 6, 4410-7	16.7	77
149	Large-area single-crystal AB-bilayer and ABA-trilayer graphene grown on a Cu/Ni(111) foil. <i>Nature Nanotechnology</i> , 2020 , 15, 289-295	28.7	76
148	Patterning metal contacts on monolayer MoS ₂ with vanishing Schottky barriers using thermal nanolithography. <i>Nature Electronics</i> , 2019 , 2, 17-25	28.4	73
147	High-performance photocurrent generation from two-dimensional WS ₂ field-effect transistors. <i>Applied Physics Letters</i> , 2014 , 104, 193113	3.4	72
146	Carrier transport at the metal-MoS ₂ interface. <i>Nanoscale</i> , 2015 , 7, 9222-8	7.7	71
145	A new mussel-inspired polydopamine phototransistor with high photosensitivity: signal amplification and light-controlled switching properties. <i>Chemical Communications</i> , 2014 , 50, 1458-61	5.8	71
144	Passivated ambipolar black phosphorus transistors. <i>Nanoscale</i> , 2016 , 8, 12773-9	7.7	70
143	A Fermi-Level-Pinning-Free 1D Electrical Contact at the Intrinsic 2D MoS ₂ -Metal Junction. <i>Advanced Materials</i> , 2019 , 31, e1808231	24	66
142	Self-assembly of Ni nanocrystals on HfO ₂ and N-assisted Ni confinement for nonvolatile memory application. <i>Applied Physics Letters</i> , 2005 , 86, 013107	3.4	61
141	Control of Etch Slope during Etching of Pt in Ar/Cl ₂ /O ₂ Plasmas. <i>Japanese Journal of Applied Physics</i> , 1996 , 35, 2501-2504	1.4	61
140	Controlled Folding of Single Crystal Graphene. <i>Nano Letters</i> , 2017 , 17, 1467-1473	11.5	60
139	Adlayer-Free Large-Area Single Crystal Graphene Grown on a Cu(111) Foil. <i>Advanced Materials</i> , 2019 , 31, e1903615	24	53
138	Ultrahigh Photoresponsive Device Based on ReS ₂ /Graphene Heterostructure. <i>Small</i> , 2018 , 14, e1802593	11	52
137	Monolayer Molybdenum Disulfide Transistors with Single-Atom-Thick Gates. <i>Nano Letters</i> , 2018 , 18, 3807-3813	11.5	52
136	Investigation of etching properties of metal nitride/high-k gate stacks using inductively coupled plasma. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2005 , 23, 964-970	2.9	51
135	Tungsten nanocrystals embedded in high-k materials for memory application. <i>Applied Physics Letters</i> , 2005 , 87, 113110	3.4	49
134	Plasma treatments to improve metal contacts in graphene field effect transistor. <i>Journal of Applied Physics</i> , 2011 , 110, 073305	2.5	48
133	Formation of Ge nanocrystals in HfAlO high-k dielectric and application in memory device. <i>Applied Physics Letters</i> , 2004 , 84, 5407-5409	3.4	47

132	Electrically Driven Reversible Phase Changes in Layered In Se Crystalline Film. <i>Advanced Materials</i> , 2017 , 29, 1703568	24	45
131	Spatial Distribution of Charge Traps in a SONOS-Type Flash Memory Using a High- κ Trapping Layer. <i>IEEE Transactions on Electron Devices</i> , 2007 , 54, 3317-3324	2.9	45
130	Investigation of electrical conduction in carbon-doped silicon oxide using a voltage ramp method. <i>Applied Physics Letters</i> , 2003 , 83, 524-526	3.4	45
129	Edge contacts of graphene formed by using a controlled plasma treatment. <i>Nanoscale</i> , 2015 , 7, 825-31	7.7	44
128	Multifunctional van der Waals Broken-Gap Heterojunction. <i>Small</i> , 2019 , 15, e1804885	11	42
127	Effects of plasma treatment on surface properties of ultrathin layered MoS ₂ . <i>2D Materials</i> , 2016 , 3, 035002	9.9	41
126	Electrical Characteristics of Memory Devices With a High- κ HfO_2 Trapping Layer and Dual $\text{SiO}_2/\text{Si}_3\text{N}_4$ Tunneling Layer. <i>IEEE Transactions on Electron Devices</i> , 2007 , 54, 2699-2705	2.9	38
125	Electrical characterization of 2D materials-based field-effect transistors. <i>2D Materials</i> , 2021 , 8, 012002	5.9	38
124	High Electric Field Carrier Transport and Power Dissipation in Multilayer Black Phosphorus Field Effect Transistor with Dielectric Engineering. <i>Advanced Functional Materials</i> , 2017 , 27, 1604025	15.6	37
123	Investigation of etching properties of HfO based high-K dielectrics using inductively coupled plasma. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2004 , 22, 1552-1558	2.9	36
122	Hybrid energy harvester based on nanopillar solar cells and PVDF nanogenerator. <i>Nanotechnology</i> , 2013 , 24, 175402	3.4	34
121	Self-assembly of Al ₂ O ₃ nanodots on SiO ₂ using two-step controlled annealing technique for long retention nonvolatile memories. <i>Applied Physics Letters</i> , 2005 , 86, 073114	3.4	33
120	High performance vertical tunneling diodes using graphene/hexagonal boron nitride/graphene hetero-structure. <i>Applied Physics Letters</i> , 2014 , 104, 053103	3.4	30
119	Electrical properties of crystalline YSZ films on silicon as alternative gate dielectrics. <i>Semiconductor Science and Technology</i> , 2001 , 16, L13-L16	1.8	30
118	Van der Waals Broken-Gap p-n Heterojunction Tunnel Diode Based on Black Phosphorus and Rhenium Disulfide. <i>ACS Applied Materials & Interfaces</i> , 2019 , 11, 8266-8275	9.5	29
117	Self-screened high performance multi-layer MoS ₂ transistor formed by using a bottom graphene electrode. <i>Nanoscale</i> , 2015 , 7, 19273-81	7.7	27
116	Reduction of metal contact resistance of graphene devices via CO ₂ cluster cleaning. <i>Applied Physics Letters</i> , 2014 , 104, 223110	3.4	27
115	Low temperature MOSFET technology with Schottky barrier source/drain, high-K gate dielectric and metal gate electrode. <i>Solid-State Electronics</i> , 2004 , 48, 1987-1992	1.7	26

114	Organic Dye Graphene Hybrid Structures with Spectral Color Selectivity. <i>Advanced Functional Materials</i> , 2016 , 26, 6593-6600	15.6	25
113	Three-dimensional metal gate-high- κ /GOI CMOSFETs on 1-poly-6-metal 0.18- μ m Si devices. <i>IEEE Electron Device Letters</i> , 2005 , 26, 118-120	4.4	25
112	Formation of SiGe nanocrystals in HfO ₂ using in situ chemical vapor deposition for memory applications. <i>Applied Physics Letters</i> , 2004 , 84, 4331-4333	3.4	25
111	High temperature platinum etching using Ti mask layer. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 1999 , 17, 2151-2155	2.9	25
110	Impact ionization by hot carriers in a black phosphorus field effect transistor. <i>Nature Communications</i> , 2018 , 9, 3414	17.4	23
109	Investigation of in situ trench etching process and Bosch process for fabricating high-aspect-ratio beams for microelectromechanical systems. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 2002 , 20, 1878		21
108	Enhancement of memory window in short channel non-volatile memory devices using double layer tungsten nanocrystals		20
107	Gate-Modulated Ultrasensitive Visible and Near-Infrared Photodetection of Oxygen Plasma-Treated WSe Lateral pn-Homojunctions. <i>ACS Applied Materials & Interfaces</i> , 2020 , 12, 23261-23271 ¹⁹	9.5	19
106	Integral control for synchronization of complex dynamical networks with unknown non-identical nodes. <i>Applied Mathematics and Computation</i> , 2013 , 224, 140-149	2.7	19
105	Frequency and Temperature Dependence of the Dielectric Properties of a PCB Substrate for Advanced Packaging Applications. <i>Journal of the Korean Physical Society</i> , 2009 , 54, 1096-1099	0.6	19
104	Dielectric Dispersion and High Field Response of Multilayer Hexagonal Boron Nitride. <i>Advanced Functional Materials</i> , 2018 , 28, 1804235	15.6	18
103	Unraveling Oxygen Transfer at the Graphene Oxide/ZnO Nanorod Interface. <i>Journal of Physical Chemistry C</i> , 2014 , 118, 17638-17642	3.8	17
102	Kinetics of particle formation in the sputtering and reactive ion etching of silicon. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 1992 , 10, 1041-1047	2.9	17
101	Phase-Engineered Molybdenum Telluride/Black Phosphorus Van der Waals Heterojunctions for Tunable Multivalued Logic. <i>ACS Applied Materials & Interfaces</i> , 2020 , 12, 14119-14124	9.5	16
100	Effects of Conductivity of Polysilicon on Profile Distortion. <i>Japanese Journal of Applied Physics</i> , 1996 , 35, 2440-2444	1.4	16
99	. <i>IEEE Transactions on Semiconductor Manufacturing</i> , 2007 , 20, 143-149	2.6	16
98	Formation of dual-phase HfO ₂ /HfSi _{1-x} O ₂ dielectric and its application in memory devices. <i>Journal of Applied Physics</i> , 2005 , 98, 013536	2.5	16
97	Lanthanide and Ir-based dual metal-gate/HfAlON CMOS with large work-function difference		16

96	High-Electric-Field-Induced Phase Transition and Electrical Breakdown of MoTe ₂ . <i>Advanced Electronic Materials</i> , 2020 , 6, 1900964	6.4	15
95	Ohmic Contact in 2D Semiconductors via the Formation of a Benzyl Viologen Interlayer. <i>Advanced Functional Materials</i> , 2019 , 29, 1807338	15.6	15
94	The device level modulation of carrier transport in a 2D WSe field effect transistor via a plasma treatment. <i>Nanoscale</i> , 2019 , 11, 17368-17375	7.7	14
93	Self-Terminated Surface Monolayer Oxidation Induced Robust Degenerate Doping in MoTe for Low Contact Resistance. <i>ACS Applied Materials & Interfaces</i> , 2020 , 12, 26586-26592	9.5	14
92	Optoelectronic Performance of Radial-Junction Si Nanopillar and Nanohole Solar Cells. <i>IEEE Transactions on Electron Devices</i> , 2012 , 59, 2368-2374	2.9	14
91	Effects of Annealing and Ar Ion Bombardment on the Removal of HfO ₂ Gate Dielectric. <i>Electrochemical and Solid-State Letters</i> , 2004 , 7, F18		14
90	Growth of plasma-generated particles and behavior of particle clouds during sputtering of silicon and silicon dioxide. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 1993 , 11, 1258-1263	2.9	14
89	Kinetics of particle generation in sputtering and reactive ion etching plasmas. <i>Applied Physics Letters</i> , 1992 , 60, 1073-1075	3.4	14
88	Low noise RF MOSFETs on flexible plastic substrates. <i>IEEE Electron Device Letters</i> , 2005 , 26, 489-491	4.4	13
87	A novel program-erasable high- κ AlN-Si MIS capacitor. <i>IEEE Electron Device Letters</i> , 2005 , 26, 148-150	4.4	13
86	Hot-Electron Capture for CHEI Programming in SONOS-Type Flash Memory Using High- κ Trapping Layer. <i>IEEE Transactions on Electron Devices</i> , 2008 , 55, 1502-1510	2.9	12
85	Partial Crystallization of HfO ₂ for Two-Bit/Four-Level SONOS-Type Flash Memory. <i>IEEE Transactions on Electron Devices</i> , 2007 , 54, 3177-3185	2.9	12
84	Study of leakage mechanisms of the copper/Black Diamond Damascene process. <i>Thin Solid Films</i> , 2004 , 462-463, 330-333	2.2	12
83	Self-assembled tungsten nanocrystals in high-k dielectric for nonvolatile memory application. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 2005 , 23, 2278		12
82	Localized Surface Plasmon Resonances by Ag Nanoparticles on SiN for Solar Cell Application. <i>Journal of the Korean Physical Society</i> , 2010 , 56, 1488-1491	0.6	12
81	Damage-Free Atomic Layer Etch of WSe: A Platform for Fabricating Clean Two-Dimensional Devices. <i>ACS Applied Materials & Interfaces</i> , 2021 , 13, 1930-1942	9.5	12
80	Endurance Reliability of Multilevel-Cell Flash Memory Using a $\text{ZrO}_2/\text{Si}_3\text{N}_4$ Dual Charge Storage Layer. <i>IEEE Transactions on Electron Devices</i> , 2008 , 55, 2361-2369	2.9	11
79	Investigation of Wet Etching Properties and Annealing Effects of Hf-Based High-k Materials. <i>Journal of the Electrochemical Society</i> , 2006 , 153, G483	3.9	11

78	Effect of large work function modulation of MoS ₂ by controllable chlorine doping using a remote plasma. <i>Journal of Materials Chemistry C</i> , 2020 , 8, 1846-1851	7.1	11
77	Fermi-Level Pinning Free High-Performance 2D CMOS Inverter Fabricated with Van Der Waals Bottom Contacts. <i>Advanced Electronic Materials</i> , 2021 , 7, 2001212	6.4	11
76	Homogeneous molybdenum disulfide tunnel diode formed via chemical doping. <i>Applied Physics Letters</i> , 2018 , 112, 183103	3.4	10
75	Enhancement of light absorption using high-k dielectric in localized surface plasmon resonance for silicon-based thin film solar cells. <i>Journal of Applied Physics</i> , 2011 , 109, 093516	2.5	10
74	Drive-Current Enhancement in FinFETs Using Gate-Induced Stress. <i>IEEE Electron Device Letters</i> , 2006 , 27, 769-771	4.4	10
73	3D GOI CMOSFETs with novel IrO ₂ /sub 2/(Hf) dual gates and high-k dielectric on 1P6M-0.18 μ m-CMOS		10
72	Formation of polycrystalline silicon germanium/HfO ₂ gate stack structure using inductively coupled plasma etching. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2003 , 21, 1210-1217	2.9	10
71	Control of the Schottky Barrier and Contact Resistance at Metal/Se ₂ Interfaces by Polymeric Doping. <i>Advanced Electronic Materials</i> , 2020 , 6, 2000616	6.4	10
70	Low-Temperature and Large-Scale Production of a Transition Metal Sulfide Vertical Heterostructure and Its Application for Photodetectors. <i>ACS Applied Materials & Interfaces</i> , 2021 , 13, 8710-8717	9.5	10
69	Fermi Level Pinning Dependent 2D Semiconductor Devices: Challenges and Prospects.. <i>Advanced Materials</i> , 2021 , e2108425	24	10
68	Self-Assembled Wire Arrays and ITO Contacts for Silicon Nanowire Solar Cell Applications. <i>Chinese Physics Letters</i> , 2011 , 28, 035202	1.8	9
67	Effects of Volatility of Etch By-products on Surface Roughness During Etching of Metal Gates in Cl ₂ . <i>Journal of the Electrochemical Society</i> , 2008 , 155, H6	3.9	9
66	Effects of SiO ₂ /Si ₃ N ₄ hard masks on etching properties of metal gates. <i>Journal of Vacuum Science & Technology B</i> , 2006 , 24, 2689		9
65	Fast erasing and highly reliable MONOS type memory with HfO ₂ high-k trapping layer and Si ₃ N ₄ /SiO ₂ tunneling stack 2006 ,		9
64	Effect of porosity on electrical stability of hydrocarbon polymeric low-k dielectric. <i>IEEE Transactions on Electron Devices</i> , 2005 , 52, 2333-2336	2.9	9
63	Charge Density Depinning in Defective MoTe ₂ Transistor by Oxygen Intercalation. <i>Advanced Functional Materials</i> , 2020 , 30, 2004880	15.6	9
62	Resonant tunnelling diodes based on twisted black phosphorus homostructures. <i>Nature Electronics</i> , 2021 , 4, 269-276	28.4	9
61	Energy Dissipation in Black Phosphorus Heterostructured Devices. <i>Advanced Materials Interfaces</i> , 2019 , 6, 1801528	4.6	9

60	Directly Probing Effective-Mass Anisotropy of Two-Dimensional ReSe ₂ in Schottky Tunnel Transistors. <i>Physical Review Applied</i> , 2020 , 13,	4.3	8
59	Sub-30 nm Strained p-Channel Fin-Type Field-Effect Transistors with Condensed SiGe Source/Drain Stressors. <i>Japanese Journal of Applied Physics</i> , 2007 , 46, 2058-2061	1.4	8
58	Process-induced particle formation in the sputtering and reactive ion etching of silicon and silicon dioxide. <i>Plasma Sources Science and Technology</i> , 1994 , 3, 273-277	3.5	8
57	High performance WSe ₂ p-MOSFET with intrinsic n-channel based on back-to-back p \bar{n} junctions. <i>Applied Physics Letters</i> , 2021 , 118, 233101	3.4	8
56	Deep level transient spectroscopy on charge traps in high-k ZrO ₂ . <i>Thin Solid Films</i> , 2010 , 518, 6382-6384	2.2	7
55	Rapid thermal oxidation of Ge-rich Si _{1-x} Ge _x heterolayers. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2006 , 24, 84-90	2.9	7
54	Anisotropic etching characteristics of platinum electrode for ferroelectric capacitor. <i>IEEE Transactions on Electron Devices</i> , 1999 , 46, 984-992	2.9	7
53	Roles of F and O Radicals and Positive Ions in a SF ₆ /O ₂ Plasma in Forming Deep Via Structures. <i>Journal of the Korean Physical Society</i> , 2009 , 54, 1774-1778	0.6	7
52	Metallic contact induced van der Waals gap in a MoS FET. <i>Nanoscale</i> , 2019 , 11, 18246-18254	7.7	6
51	High carrier mobility in Si-MOSFETs with a hexagonal boron nitride buffer layer. <i>Solid State Communications</i> , 2015 , 209-210, 1-4	1.6	6
50	Multi-level cell storage with a modulated current method for phase-change memory using Ge-doped SbTe. <i>Current Applied Physics</i> , 2011 , 11, e79-e81	2.6	6
49	SELF-ASSEMBLY OF SI NANOSTRUCTURES IN SF ₆ /O ₂ PLASMA. <i>Nano</i> , 2008 , 03, 169-173	1.1	6
48	Effects of N ₂ , O ₂ , and Ar plasma treatments on the removal of crystallized HfO ₂ film. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2006 , 24, 133-140	2.9	6
47	. <i>IEEE Transactions on Electron Devices</i> , 2010 , 57, 2794-2800	2.9	5
46	Pulse-agitated self-convergent programming for 4-bit per cell dual charge storage layer flash memory. <i>Solid-State Electronics</i> , 2010 , 54, 14-17	1.7	5
45	Reliability improvement using buried capping layer in advanced interconnects		5
44	Enhancement of adhesion strength of Cu layer on single and multi-layer dielectric film stack in Cu/low k multi-level interconnects. <i>Microelectronic Engineering</i> , 2004 , 75, 183-193	2.5	5
43	In situ trench etching and releasing technique of high aspect ratio beams using magnetically enhanced reactive ion etching. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 2002 , 20, 154		5

42	Chemical Dopant-Free Doping by Annealing and Electron Beam Irradiation on 2D Materials. <i>Advanced Electronic Materials</i> , 2100449	6.4	5
41	Formation of PtSi Schottky barrier MOSFETs using plasma etching. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2015 , 33, 021307	2.9	4
40	Effect of electric field on chemical bonds of carbon-doped silicon oxide as evidenced by in situ Fourier transform infrared spectroscopy. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 2005 , 23, 433		4
39	Effects of Nanostructures Formed by Plasma Etching on the Reflectance of Solar Cells. <i>Journal of the Korean Physical Society</i> , 2009 , 54, 1016-1020	0.6	4
38	High carrier mobility in graphene doped using a monolayer of tungsten oxyselenide. <i>Nature Electronics</i> , 2021 , 4, 731-739	28.4	4
37	Modified write-and-verify scheme for improving the endurance of multi-level cell phase-change memory using Ge-doped SbTe. <i>Solid-State Electronics</i> , 2012 , 76, 67-70	1.7	3
36	. <i>IEEE Transactions on Electron Devices</i> , 2011 , 58, 3254-3259	2.9	3
35	V_{th} Control by Complementary Hot-Carrier Injection for SONOS Multi-Level Cell Flash Memory. <i>IEEE Transactions on Electron Devices</i> , 2009 , 56, 3027-3032	2.9	3
34	Novel ZrO ₂ /Si ₃ N ₄ Dual Charge Storage Layer to Form Step-Up Potential Wells for Highly Reliable Multi-Level Cell Application 2007 ,		3
33	Simulation of trapping properties of high ϵ material as the charge storage layer for flash memory application. <i>Thin Solid Films</i> , 2006 , 504, 209-212	2.2	3
32	Mechanism of particle formation in the sputtering and reactive ion etching of Si and SiO ₂ . <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1994 , 12, 2758		3
31	Temperature of a Semiconducting Substrate Exposed to an Inductively Coupled Plasma. <i>Journal of the Korean Physical Society</i> , 2011 , 59, 262-270	0.6	3
30	Metal/Insulator Transition Driven by Traps in 2D WSe ₂ Field-Effect Transistor. <i>Advanced Electronic Materials</i> , 2200046	6.4	3
29	Ultrahigh Anisotropic Transport Properties of Black Phosphorus Field Effect Transistors Realized by Edge Contact. <i>Advanced Electronic Materials</i> , 2022 , 8, 2100988	6.4	3
28	Second-Bit-Effect-Free Multibit-Cell Flash Memory Using $\text{Si}_3\text{N}_4/\text{ZrO}_2$ Split Charge Trapping Layer. <i>IEEE Transactions on Electron Devices</i> , 2009 , 56, 1966-1973	2.9	2
27	Low energy N ₂ ion bombardment for removal of (HfO ₂) _x (SiON) _{1-x} in dilute HF. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2007 , 25, 1056-1061	2.9	2
26	Chemical analysis of etching residues in metal gate stack for CMOS process. <i>Studies in Surface Science and Catalysis</i> , 2006 , 159, 365-368	1.8	2
25	Reactive Ion Etching of Copper with SiCl ₄ and CCl ₂ F ₂ . <i>Materials Research Society Symposia Proceedings</i> , 1990 , 201, 129		2

24	Application of the Black Silicon Phenomenon to Forming High-Aspect-Ratio Deep Vias. <i>Journal of the Korean Physical Society</i> , 2009 , 54, 616-620	0.6	2
23	Traps at the hBN/WSe ₂ interface and their impact on polarity transition in WSe ₂ . <i>2D Materials</i> , 2021 , 8, 035027	5.9	2
22	Analytical measurements of contact resistivity in two-dimensional WSe ₂ field-effect transistors. <i>2D Materials</i> , 2021 , 8, 045019	5.9	2
21	High photocurrent and quantum efficiency of graphene photodetector using layer-by-layer stack structure and trap assistance 2012 ,		1
20	A time-dependent technique for carrier recombination and generation lifetime measurement in SOI MOSFET. <i>Solid-State Electronics</i> , 2008 , 52, 1773-1777	1.7	1
19	Integrated process of photoresist trimming and dielectric hard mask etching for sub-50 nm gate patterning. <i>Thin Solid Films</i> , 2006 , 504, 117-120	2.2	1
18	Novel HfAlO charge trapping layer in SONOS type flash memory for multi-bit per cell operation 2006 ,		1
17	Chemical Vapor Deposition of Germanium Nanocrystals on Hafnium Oxide for Non-Volatile Memory Applications. <i>Materials Research Society Symposia Proceedings</i> , 2004 , 830, 299		1
16	Direct trim etching process of Si/SiO ₂ gate stacks using 193 nm ArF patterns. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2004 , 22, 1500-1505	2.9	1
15	Contact Resistivity in Edge-Contacted Graphene Field Effect Transistors. <i>Advanced Electronic Materials</i> , 2101169	6.4	1
14	Anomalously persistent p-type behavior of WSe ₂ field-effect transistors by oxidized edge-induced Fermi-level pinning. <i>Journal of Materials Chemistry C</i> , 2022 , 10, 846-853	7.1	1
13	Edge Rich Ultrathin Layered MoS Nanostructures for Superior Visible Light Photocatalytic Activity.. <i>Langmuir</i> , 2022 ,	4	1
12	Recent progress in 1D contacts for 2D material-based devices.. <i>Advanced Materials</i> , 2022 , e2202408	24	1
11	Removal of Plasma-Induced Physical Damage Formed in Nanoscale Three-Dimensional FinFETs. <i>Nano</i> , 2017 , 12, 1750099	1.1	0
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